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# OCTAL ±100V 2A 3-LEVEL ULTRASOUND PULSER

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The ABLIC Inc. HDL6M05584 is an octal, 3-level RTZ, high-voltage, high-speed ultrasound pulser. The HDL6M05584 comprises logic interfaces, level translators, MOSFET gate drive buffers with floating voltage regulators, high-voltage, high-current MOSFETs, and active T/R switches.

#### **Functions**

• Octal 3-level pulser with active T/R switch with 2-input per channel

#### **Features**

- 0 to ±100V output voltage
- ±2A source and sink peak current for pulsing (V<sub>PP</sub>/V<sub>NN</sub>)
- ±1A source and sink peak current for active ground clamp
- 250Ω (±0.1A) active ground clamp without blocking diode for anti-leakage (Analog SW type)
- Embedded floating voltage regulators
- Symmetrical positive and negative pulse waveforms for low 2<sup>nd</sup> order harmonic distortion
- Up to 200MHz LVDS/LVCMOS clock (transparent mode available)
- 15Ω active T/R switch with 2-bit turn-on timing control
- 20MHz output frequency @±60V output, 220pF load
- 1.8V to 5V CMOS logic interface
- Noise-cut diodes at each high-voltage output
- Embedded high-voltage clamp diodes
- 4-mode output current control
- Automatic thermal protection with indicator
- Power-up/down reset function for free power sequencing and for fail-safe in abrupt power drop
- Latch-up free, low crosstalk between channels by SOI CMOS technology
- 64-lead 9x9mm QFN package (RoHS compliant)

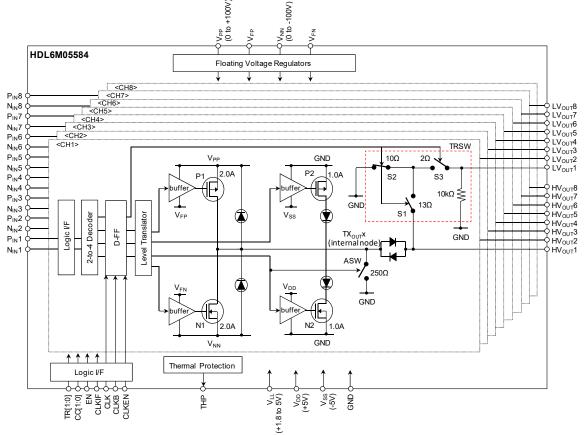


Fig.1 Block diagram

# 1. Absolute Maximum Ratings

 $T_A$ =25°C unless otherwise noted.

Table 1 Absolute Maximum Ratings

No.	Items	Symbol	Value	Units	Condition
1	Logic supply voltage	V <sub>LL</sub>	-0.4 to +7	V	
2	Positive supply voltage	$V_{DD}$	-0.4 to +7	V	
3	Negative supply voltage	Vss	-7 to +0.4	V	
4	Positive high-voltage supplies	V <sub>PP</sub>	-0.5 to +105	V	
5	Negative high-voltage supplies	V <sub>NN</sub>	-105 to +0.5	V	
6	High-voltage outputs (x=1~8)	HV <sub>оит</sub> х	-105 to +105	V	
7	Low-voltage outputs (x=1~8)	LV <sub>OUT</sub> X	-1 to +1	V	
8	THP (Thermal Protection) output	THP	-0.4 to +7	V	
9	All Logic input voltages (x=1~8)	PINX, NINX, EN, CLKEN, CLK, CLKB, CLKIF, CC[1:0], TR[1:0]	-0.4 to +7	V	
10	Operating junction temperature	TJop	-20 to +150	°C	
11	Operating free-air Temperature	T <sub>A</sub>	0 to +75	°C	
12	Storage temperature	T <sub>STG</sub>	-55 to +150	°C	
13	Maximum power dissipation	P <sub>Dmax</sub>	4	W	

NOTE: Stresses beyond the absolute maximum ratings may cause permanent damage to the product.

# 2. Operating Supply Voltages, Logic Inputs, and Power sequencing

#### 2.1 Operating Supply Voltages

Table 2 Operating Supply Voltages

No	Items	Symbol	Min	Тур	Max	Units	Condition
	I ania augustus litana	\/	2.4	2.5 to 3.3	3.6	V	Clock mode
'	Logic supply voltage	$V_{LL}$	1.7	1.8 to 5	$V_{\text{DD}}$	V	Transparent mode
2	Positive supply voltage	$V_{DD}$	4.75	5	5.25	V	
3	Negative supply voltage	V <sub>SS</sub>	-5.25	-5	-4.75	V	
4	Positive high-voltage supplies	$V_{PP}$	0	-	100	V	
5	Negative high-voltage supplies	$V_{NN}$	-100	-	0	V	
6	IC substrate voltage *	V <sub>SUB</sub>	-	0	-	V	
7	V <sub>PP</sub> , V <sub>NN</sub> slew rate	$SR_MAX$	-	-	25	V/ms	

NOTE: \* The package exposed pad internally connected to the chip substrate must be soldered to the ground.

#### 2.2 Logic Inputs

Clock (CLK) mode synchronizes data inputs P<sub>INX</sub>, N<sub>INX</sub> (x=1~8) with a differential LVDS/CMOS clock. Transparent (TP) mode without using clock is also available.

#### CLK mode:

Set CLKEN=0. P<sub>IN</sub>x and N<sub>IN</sub>x are decoded, clocked, level-translated, then sent to high-voltage output stage. Differential clock input has two modes as shown below.

- LVDS CLK mode: set CLKIF=0. Connect 100Ω between CLK and CLKB. See Table 3 and 4 for the logic inputs, CLK, and CLKB.
- CMOS CLK mode: set CLKIF=1. See Table 3 for all the logic inputs.

#### TP mode:

Set CLKEN=CLKIF=1, CLK=CLKB=0.  $P_{IN}x$  and  $N_{IN}x$  are decoded, level-translated, then sent to high-voltage output stage. See Table 3 for all the logic inputs.

No Items Symbol Min Тур Max Units Condition 1 High-level logic input voltage  $V_{IH}$  $0.8V_{LL}$  $V_{LL}$ V  $0.2V_{LL}$ ٧ 2 Low-level logic input voltage  $V_{\mathsf{IL}}$ 0 3 Logic input capacitance CIN 3 pF Logic input high current \*1 -10 10 lін μΑ 5 Logic input low current \*2 lιL -10 10 μΑ CMOS CLK mode 800 ps CLK≥100MHz Input rise/fall time tr, tf 10~90% CLK, CLKB, 2.0 CLK<100MHz ns Pinx, Ninx Input clock frequency 200 fclk MHz CMOS CLK mode, CLK, CLKB, %  $f_{CLK}=1/T$ ,  $D_{CLK}=\tau/T$ , See Fig.3 Duty cycle Dclk 40 50 60 Data Setup time 9 1.4 tsu ns CLK mode, Pinx, Ninx to CLK/CLKB 10 Data Hold time See Fig.3 1.4 t<sub>HLD</sub> ns

Table 3 Logic Inputs

#### NOTE:

<sup>\*2)</sup> EN, CC[1:0], CLKEN, and CLKIF have 50μA leakage at V<sub>LL</sub>=2.5V due to 50kΩ internal pull-up resistor.

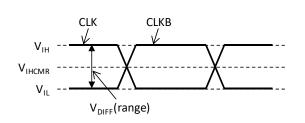
No	Items	Symbol	Min	Тур	Max	Units	Condition
1	High-level input voltage	V <sub>IH</sub>	1.265	-	-	V	VIHCMR(Typ)+VDIFF(Min)/2
2	Low-level input voltage	VIL	ı	•	1.135	V	VIHCMR(Typ)-VDIFF(Min)/2
3	Differential input voltage range	V <sub>DIFF(range)</sub>	0.13	0.35	0.49	±V	same as CLK,CLKB voltage swing See Fig.2
4	Differential input voltage peak to peak swing	$V_{DIFF(p\text{-}p)}$	0.26	0.7	0.98	V <sub>pp</sub>	CLK-CLKB  differential peak-to-peak voltage swing, See Fig.2
5	Input voltage common mode range	VIHCMR	0.84	1.2	1.56	V	
6	Differential input impedance	R <sub>IN</sub>	85	100	115	Ω	
7	High-level input current	liH	ı	ı	5.8	mA	
8	Low-level input current	IιL	ı	ı	5.8	mA	
9	Input rise/fall time	t <sub>r</sub> , t <sub>f</sub>	-	-	600	ps	20% to 80% of V <sub>DIFF</sub>
10	Input clock frequency	fclk	-	ı	200	MHz	LVDS CLK mode, CLK, CLKB,
11	Duty cycle	D <sub>CLK</sub>	40	50	60	%	f <sub>CLK</sub> =1/T, D <sub>CLK</sub> =τ/T, See Fig.3

NOTE: Please refer to table 3 for the logic inputs other than CLK, CLKB in LVDS CLK mode.

<sup>\*1)</sup> TR[1:0] have 50 $\mu$ A leakage at VLL=2.5V due to 50k $\Omega$  internal pull-down resistor.

Differential input voltage range (VDIFF(range))

Differential input voltage peak to peak swing (VDIFF(p-p))



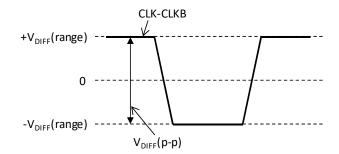


Fig.2 LVDS clock inputs

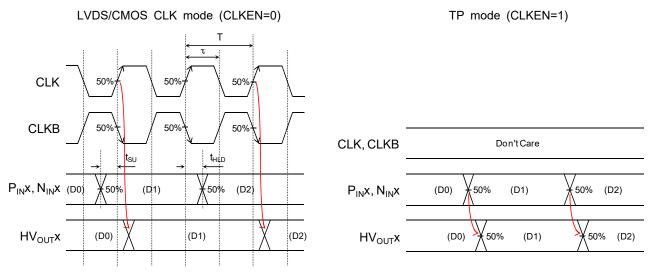


Fig.3 Setup/Hold Time

#### 2.3 Power Supply Sequencing

Embedded low-voltage (LV) power-up/down reset function provides free power supply sequencing.

It also provides fail-safe system in abrupt LV power supply drop.

When any one of LV power supplies is turned off during operation, all internal circuits will be immediately reset, and both inputs and outputs will be disabled.

Once all LV power supplies are restored, both inputs and outputs will be enabled.

# 3. Typical Application Circuit

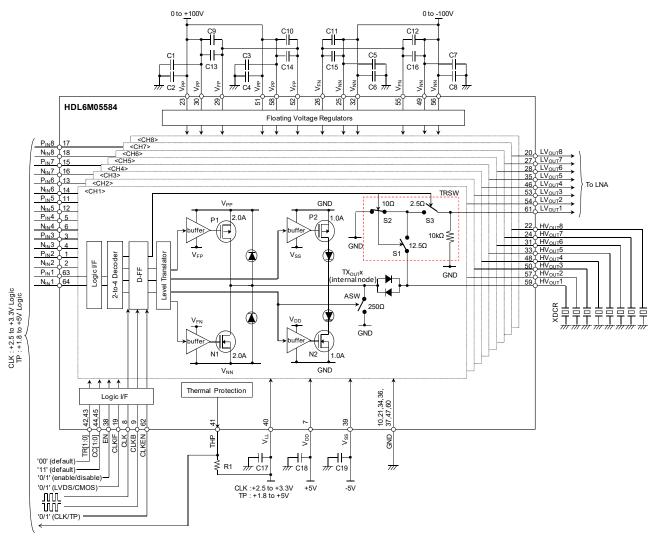


Fig.4 Typical Application Circuit

#### Note:

- 1. High-voltage power supply pins, V<sub>PP</sub>/V<sub>NN</sub>, can draw fast transient currents up to ±2.0A. Therefore, ceramic capacitors of ≥200V 0.1μF to 1μF (C1~8) should be connected as close to the pins as possible for bypassing purpose.
- 2. Ceramic capacitors of ≥16V 10µF (C9~12), ≥16V 100nF (C13~16), and ≥16V 0.1µF to 1µF (C17~19) should also be connected between high-voltage power supply pins and corresponding floating voltage pins V<sub>FP</sub>/V<sub>FN</sub>, and low-voltage power supply pins for bypassing purpose. Connect those as close to the pins as possible.
- 3. It is also important to minimize the trace length and to have enough trace width of those high voltage and floating voltage lines.
- 4. The thermal tab on the bottom of the package must be soldered to the GND.
- 5. Please refer to Mode Control Tables for detailed CC[1:0] and TR[1:0] setting.

#### 4. Electrical Characteristics

# 4.1 Operating Supply Currents

Table 5 Operating Supply Currents

 $V_{LL} = 2.5 V, \ V_{DD} / V_{SS} = +/-5 V, \ T_A = 25 ^{\circ} C, \ CLK = CLKB = 100 MHz / 0 (CLKEN = 0/1), \ TR[1:0] = '00', \ T_A = 100 MHz / 0 (CLKEN = 0/1), \ TR[1:0] = 100 MHz /$ 

HVout load=220pF//200 $\Omega$ , LVout load=47pF//200 $\Omega$ , unless otherwise specified.

NI-	14		0		Spec		11	0
No.	ile	ms	Symbol	Min	Тур	Max	Units	Conditions
		TP		-	0.03	-	mA	Quiescent current-1
1	V <sub>LL</sub> current	LVDS CLK	ILLQD	•	0.08	-	mA	
		CMOS CLK		•	0.13	-	mA	EN=1(Disable)
		TP		ı	2.8	-	mA	P <sub>IN</sub> x=N <sub>IN</sub> x=0 Current mode 3 (CC[1:0]='11')
2	V <sub>DD</sub> current	LVDS CLK	IDDQD	•	2.8	-	mA	V <sub>PP</sub> /V <sub>NN</sub> =+/-100V
		CMOS CLK		-	2.8	-	mA	, 1001
3	V <sub>SS</sub> current		Issqd	-	0.63	-	mA	
4	V <sub>PP</sub> current		IPPQD	•	0.03	-	mA	
5	V <sub>NN</sub> current		I <sub>NNQD</sub>	-	0.04	-	mA	
		TP		-	0.08	-	mA	Quiescent current-2
6	V <sub>LL</sub> current	LVDS CLK	ILLQE	-	0.18	-	mA	
		CMOS CLK		-	0.13	-	mA	EN=0(Enable) P <sub>IN</sub> x=N <sub>IN</sub> x=0
		TP		-	10	-	mA	Current mode 3 (CC[1:0]='11')
7	V <sub>DD</sub> current	LVDS CLK	IDDQE	-	30	-	mA	VPP/VNN=+/-100V
		CMOS CLK		-	28	-	mA	
8	V <sub>SS</sub> current		Issqe	-	9.3	-	mA	
9	V <sub>PP</sub> current		IPPQE	-	0.15	-	mA	
10	V <sub>NN</sub> current		I <sub>NNQE</sub>	-	0.15	-	mA	
		TP		-	0.08	-	mA	PW operating current
11	V <sub>LL</sub> current	LVDS CLK	ILLPW	•	0.18	-	mA	
		CMOS CLK		-	0.13	-	mA	EN=0
		TP		•	10	-	mA	Current mode 3 (CC[1:0]='11') 8-channel active
12	V <sub>DD</sub> current	LVDS CLK	I <sub>DDPW</sub>	•	34	-	mA	Bipolar 3-level 2-cycle
		CMOS CLK		•	32	-	mA	f=5MHz, PRT=200µs
13	3 V <sub>SS</sub> current		Isspw	-	9.3	-	mA	V <sub>PP</sub> /V <sub>NN</sub> =+/-60V
14	V <sub>PP</sub> current		IPPPW	-	4.2	-	mA	
15	V <sub>NN</sub> current		I <sub>NNPW</sub>	-	4.9	-	mA	

Table 5 Operating Supply Currents (continued)

					Spec			0 1111	
No.	Ite	ms	Symbol	Min	Тур	Max	Units	Conditions	
		TP		-	0.43	-	mA	CW operating current-1	
16	V <sub>LL</sub> current	LVDS CLK	ILLCW3	-	0.53	1	mA		
		CMOS CLK		-	0.48	-	mA	EN=0	
		TP		-	42	-	mA	Current mode 3 (CC[1:0]='11')	
17	V <sub>DD</sub> current	LVDS CLK	I <sub>DDCW3</sub>	-	64	-	mA	8-channel active Bipolar 3-level Continuous	
		CMOS CLK		-	61	-	mA	f=5MHz	
18	Vss current		Isscw3	-	27	-	mA	V <sub>PP</sub> /V <sub>NN</sub> =+/-5V	
19	VPP current		<b>І</b> РРСW3	-	217	-	mA		
20	V <sub>NN</sub> current		I <sub>NNCW3</sub>	-	220	-	mA		
		TP		-	0.48	-	mA	CW operating current-2	
21	V <sub>LL</sub> current	LVDS CLK	I <sub>LLCW2</sub>	-	0.58	1	mA		
		CMOS CLK		-	0.53	1	mA	EN=0	
		TP		-	38	1	mA	Current mode 2 (CC[1:0]='10') 8-channel active	
22	V <sub>DD</sub> current	LVDS CLK	I <sub>DDCW2</sub>	-	60	-	mA	Bipolar 3-level Continuous	
		CMOS CLK		-	57	1	mA	f=5MHz	
23	Vss current		Isscw <sub>2</sub>	-	23	1	mA	V <sub>PP</sub> /V <sub>NN</sub> =+/-5V	
24	V <sub>PP</sub> current		I <sub>PPCW2</sub>	-	208	1	mA		
25	V <sub>NN</sub> current		I <sub>NNCW2</sub>	-	211	1	mA		
		TP		-	0.48	ı	mA	CW operating current-3	
26	VLL current	LVDS CLK	ILLCW1	-	0.58	-	mA		
		CMOS CLK		-	0.53	-	mA	EN=0	
		TP		-	34	-	mA	Current mode 1 (CC[1:0]='01') 8-channel active	
27	V <sub>DD</sub> current	LVDS CLK	I <sub>DDCW1</sub>	-	56	1	mA	Bipolar 3-level Continuous	
		CMOS CLK		-	53	1	mA	f=5MHz	
28	Vss current		Isscw <sub>1</sub>	-	18	1	mA	V <sub>PP</sub> /V <sub>NN</sub> =+/-5V	
29	V <sub>PP</sub> current		I <sub>PPCW1</sub>	-	195	1	mA		
30	V <sub>NN</sub> current		I <sub>NNCW1</sub>	-	198	1	mA		
		TP		-	0.53	1	mA	CW operating current-4	
31	V <sub>LL</sub> current	LVDS CLK	ILLCW0	-	0.63	-	mA		
		CMOS CLK		-	0.58	-	mA	EN=0	
		TP		-	28	-	mA	Current mode 0 (CC[1:0]='00') 8-channel active	
32	V <sub>DD</sub> current	LVDS CLK	IDDCW0	-	49	-	mA	Bipolar 3-level Continuous	
		CMOS CLK		-	47	-	mA	f=5MHz	
33	Vss current		Isscwo	-	13	-	mA	V <sub>PP</sub> /V <sub>NN</sub> =+/-5V	
34	V <sub>PP</sub> current		I <sub>PPCW0</sub>	-	169	-	mA		
35	V <sub>NN</sub> current		I <sub>NNCW0</sub>	-	173	-	mA		

#### 4.2 Static Characteristics

#### Table 6 Static Characteristics

 $\label{eq:Vll} V_{LL}\text{=}2.5V,\ V_{DD}/V_{SS}\text{=+/-5V},\ T_{A}\text{=}25^{o}C,\ unless\ otherwise\ specified.}$ 

				Spec			
No.	Items	Symbol	Min	Тур	Max	Units	Conditions
1	HVou⊤x output voltage range	НVоитх	-100	-	+100	V	
				2.0	-	Α	V <sub>PP</sub> /V <sub>NN</sub> =+/-60V
							Current mode 3 (CC[1:0]='11')
			-	1.5	-	Α	V <sub>PP</sub> /V <sub>NN</sub> =+/-60V Current mode 2 (CC[1:0]='10')
2	HV <sub>OUT</sub> x high-side peak current	n-side peak current IOH		V <sub>PP</sub> /V <sub>NN</sub> =+/-60V			
			-	1.0	-	Α	Current mode 1 (CC[1:0]='01')
			-	0.5	-	Α	V <sub>PP</sub> /V <sub>NN</sub> =+/-60V
	HV <sub>OUT</sub> x high-side GND clamp	_				_	Current mode 0 (CC[1:0]='00')
3	peak current	Іонсь	-	1.0	-	Α	V <sub>PP</sub> /V <sub>NN</sub> =+/-60V
			_	2.0	_	Α	V <sub>PP</sub> /V <sub>NN</sub> =+/-60V
							Current mode 3 (CC[1:0]='11')
			-	1.5	-	Α	V <sub>PP</sub> /V <sub>NN</sub> =+/-60V Current mode 2 (CC[1:0]='10')
4	HV <sub>OUT</sub> x low-side peak current	lol		1.0		۸	V <sub>PP</sub> /V <sub>NN</sub> =+/-60V
			-	1.0	-	Α	Current mode 1 (CC[1:0]='01')
			-	0.5	-	Α	V <sub>PP</sub> /V <sub>NN</sub> =+/-60V
	HVoutx low-side GND clamp						Current mode 0 (CC[1:0]='00')
5	peak current	lolcl	-	1.0	-	Α	V <sub>PP</sub> /V <sub>NN</sub> =+/-60V
				10	•	Ω	I <sub>OH</sub> =100mA
		ŀ					Current mode 3 (CC[1:0]='11')
			-	13	-	Ω	I <sub>OH</sub> =100mA Current mode 2 (CC[1:0]='10')
6	HV <sub>OUT</sub> x high-side on-resistance	Ronh		40			I <sub>OH</sub> =100mA
			-	18	-	Ω	Current mode 1 (CC[1:0]='01')
			-	31	_	Ω	I <sub>он</sub> =100mA
	HV <sub>OUT</sub> x high-side GND clamp						Current mode 0 (CC[1:0]='00')
7	on-resistance	RONHCL	-	21	-	Ω	I <sub>OHCL</sub> =100mA
			_	9	_	Ω	I <sub>OL</sub> =100mA
		}				32	Current mode 3 (CC[1:0]='11')
			-	12	-	Ω	I <sub>OL</sub> =100mA Current mode 2 (CC[1:0]='10')
8	HV <sub>OUT</sub> x low-side on-resistance	RONL		47			I <sub>OL</sub> =100mA
			-	17	-	Ω	Current mode 1 (CC[1:0]='01')
		-	_	30	-	Ω	I <sub>OL</sub> =100mA
	HVoutx low-side GND clamp						Current mode 0 (CC[1:0]='00')
9	on-resistance	Ronlcl	-	20	-	Ω	I <sub>OLCL</sub> =100mA
10	HV <sub>OUT</sub> x off-capacitance	CHVOFF	-	20	-	pF	TX <sub>OUT</sub> X=GND, TRSW=off

# 4.3 Dynamic Characteristics

Table 7 Dynamic Characteristics

 $V_{LL} = 2.5V, \ V_{DD}/V_{SS} = +/-5V, \ V_{PP}/V_{NN} = +/-60V, \ T_A = 25^{\circ}C, \ TR[1:0] = '00', \ CC[1:0] = '11', \ T_{NN} = +/-60V, \ T_{N$ 

 $CLK = CLKB = 100MHz/0 (CLKEN = 0/1), \ HV{\scriptsize out\ load} = 220pF//200\Omega, \ LV{\scriptsize out\ load} = 47pF//200\Omega, \ unless \ otherwise \ specified.$ 

	No. Itama		0 1 1		Spec			Conditions	
No.	Items		Symbol	Min	Тур	Max	Units	Conditions	
1	Output frequency		fоит	-	20	-	MHz		
2	Output rise	TP mode	4.	-	31	-	ns	See Fig.5	
2	propagation delay	CLK mode	t <sub>dr</sub>	-	37	-	ns		
3	Output fall	TP mode	t <sub>df</sub>	-	31	-	ns		
	propagation delay	CLK mode	Lat	-	37	-	ns		
4	Output rise	TP mode	<b>t</b> drCL	-	31	-	ns		
_	propagation delay clamp	CLK mode	Larce	-	37	-	ns		
5	Output fall	TP mode	t <sub>dfCL</sub>	-	31	-	ns		
	propagation delay clamp	CLK mode	taice	-	37	-	ns		
6	Propagation delay matchi	ng	$\Delta t_{\text{d}}$	-	±1	±3	ns		T
				-	16	-	ns	CC[1:0]='11'	
			t <sub>r</sub>	-	24	-	ns	CC[1:0]='10'	
7	Output rise time		Li .	-	34	-	ns	CC[1:0]='01'	
				-	44	-	ns	CC[1:0]='00'	
		<b>t</b> rCL	-	25	-	ns		See	
			-	16	-	ns	CC[1:0]='11'	Fig.5	
	Output fall time		t <sub>f</sub>	-	24	-	ns	CC[1:0]='10'	
8			ч	-	34	-	ns	CC[1:0]='01'	
				-	44	-	ns	CC[1:0]='00'	
			$t_fCL$	-	25	-	ns		
9	2 <sup>nd</sup> harmonic distortion		HD2	-	-40	-	dBc	Bipolar, 2-cyc, f <sub>OUT</sub> =5MHz	
10	Pulse cancellation		HDPC	-	-40	-	dBc	See Fig.6	
10	T disc caricellation		HDPC2	-	-40	-	dBc		
11	RMS output jitter		t₃	-	10	-	ps	Bipolar CW, $f_{OUT}$ =5MHz V <sub>PP</sub> /V <sub>NN</sub> =+/-5V	
12	Crosstalk between channe	els	XTLK	-	-70	-	dB	$f_{OUT}$ =5MHz, $10V_{p-p}$ , $HV_{OUT}$ load=50 $\Omega$	
		TP		-	31	-	ns	See Fig.7	
13	Output enable time	LVDS CLK	t <sub>EN</sub>	-	120	-	ns		
		CMOS CLK		-	140	-	ns		
14	Output disable time	tos	-	37	-	ns			
15	Clock mode enable time	tclken	-	37	-	ns			
16	Clock mode disable time		tclkds	-	37	-	ns		

### 4.4 Integrated Peripheral Circuits Characteristics

#### T/R Switch

#### Table 8 T/R Switch Characteristics

 $V_{LL}$ =2.5V,  $V_{DD}/V_{SS}$ =+/-5V,  $V_{PP}$ 1/ $V_{NN}$ 1= $V_{PP}$ 2/ $V_{NN}$ 2=+/-60V,  $V_{A}$ =25°C, unless otherwise specified.

NIa	ltomo		Currele el		Spec		11	0	
No.	Items		Symbol	Min	Тур	Max	Units	Conditions	
1	LV <sub>OUT</sub> x output voltage ra	ange	LV <sub>OUT</sub> x	-0.85	ı	+0.85	V		
2	TRSW on-resistance		Rontr	1	15	-	Ω	HV <sub>OUT</sub> x=100mV, LV <sub>OUT</sub> x=0V	
3	TRSW on-capacitance		Contr	ı	12	-	pF	LV <sub>OUT</sub> x=0V	
4	TRSW off-resistance o	n HVOUTx	Rofftrhv	1	1	-	МΩ		
5	TRSW off-resistance o	FRSW off-resistance on LVOUTx		8	10	12	kΩ		
6	Spike voltage		$V_{TRN}$			50	тVрр	50pF// $200$ Ω load on HV <sub>OUT</sub> X	
	on HVoutx and LVout	(						20pF//200Ω load on LV <sub>OUT</sub> x	
		TR[1:0]='00'		-	300	-	ns	Logic input-to-ready for Rx signal	
7	TRSW turn-on time	TR[1:0]='01'	timon	-	400	-	ns	See Fig.8	
'	TROW turn-on time	TR[1:0]='10'	t <sub>dTRON</sub>	ı	500	-	ns		
		TR[1:0]='11'		-	600	-	ns		
8	TRSW turn-off time		tdTROFF	1	50	100	ns	See Fig.8	
9	Tx setup time		t <sub>TXSU</sub>	100	-	-	ns	P <sub>IN</sub> x=N <sub>IN</sub> x=0 (GND) for at least 100ns before Tx burst. See Fig.8	

# Analog Switch

#### Table 9 Analog Switch Characteristics

### T<sub>A</sub>=25°C

NIa	Items	Symbol		Spec		l lucita	Conditions
No.			Min	Тур	Max	Units	
1	ASW on-resistance	Ronasw	-	250	-	Ω	

### HV Blocking Diode

### Table 10 Output HV Blocking Diode Characteristics

T<sub>A</sub>=25°C

Nia	Items	Symbol		Spec		Units	Conditions
No.			Min	Тур	Max	Units	Conditions
	Forward voltage	V <sub>FHVD</sub>	-	1.0	-	V	I <sub>F</sub> =100mA
I			i	1.2	-	V	I <sub>F</sub> =200mA
2	Reverse voltage	VRHVD	200	-	-	V	I <sub>R</sub> =1µA

#### LV Noise-cut Diode

#### Table 11 Output LV Noise-cut Diode Characteristics

T<sub>A</sub>=25°C

NI-	Items	Symbol		Spec		Lluita	Conditions
No.			Min	Тур	Max	Units	
4	Forward voltage	V <sub>FLVD</sub>	-	1.1	-	V	I <sub>F</sub> =100mA
1			-	1.25	-	V	I <sub>F</sub> =200mA

#### Thermal Protection

#### Table 12 Thermal Protection Characteristics

 $V_{LL} \! = \! 2.5 V, \ V_{DD} \! / V_{SS} \! = \! + \! / \! - \! 5 V, \ T_A \! = \! 25^{o}C, \ unless \ otherwise \ specified.$ 

NI-	14	0	Spec			Linita	0 133
No.	Items	Symbol	Min	Тур	Max	Units	Conditions
1	THP pull-up voltage	V <sub>PUTHP</sub>	-	-	5.25	V	Open drain
2	THP output current	I <sub>THP</sub>	ı	1.0	ı	mA	-
3	THP output low voltage	VOLTHP	ı	-	0.5	<b>V</b>	THP active, V <sub>LL</sub> =2.5V, I <sub>THP</sub> =1mA
4	THP temperature threshold	Ттнр	90	110	130	ç	
5	THP reset hysteresis	Тнүзтнр	-	10	-	°C	

# 5. Switching Time Diagram

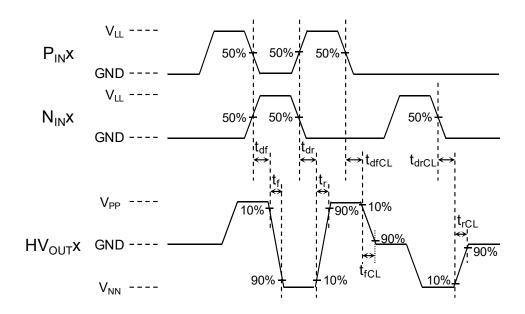
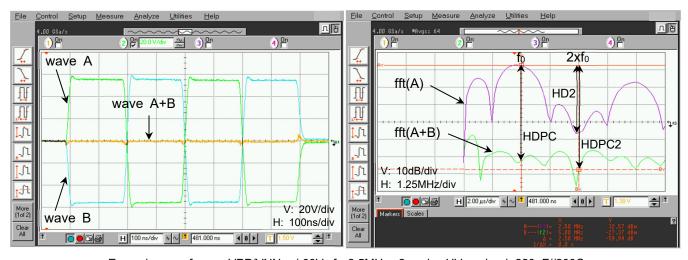


Fig.5 Propagation delay and Output rise/fall time



Example waveforms: VPP/VNN=+/-60V, fo=2.5MHz, 2-cycle, HVout load=220pF//200 $\Omega$ 

Fig.6 2<sup>nd</sup> harmonic distortion and Pulse cancellation

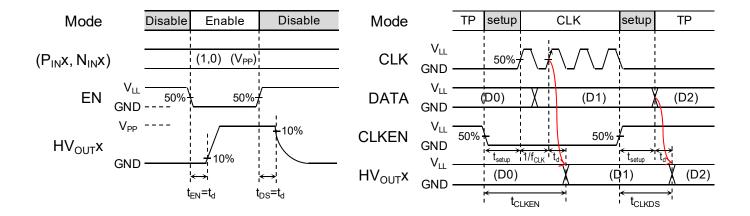


Fig.7 Output enable/disable and Clock enable/disable time

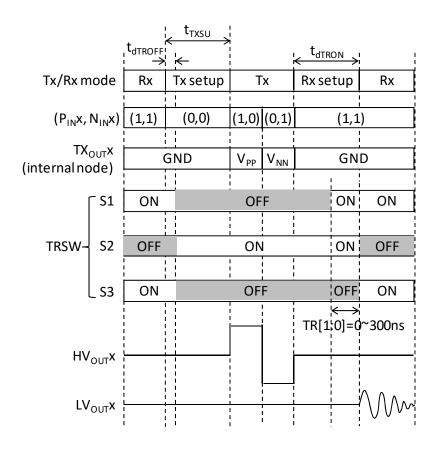


Fig.8 T/R Switch turn-on/off time

#### 6. Truth Table and Mode Control tables

Table 13 Truth table

Lo	ogic Inpi	uts		Internal MOSFET state				Outpu	t state			
EN	P <sub>IN</sub> x	N <sub>IN</sub> x	P1	N1	P2	N2	ASW		TRSW		TX <sub>OUT</sub> x	LV <sub>OUT</sub> x
			+HV	-HV	GND	GND	GND	S1	S2	S3	(internal node)	
0	0	0	OFF	OFF	ON	ON	ON	OFF	ON	OFF	GND	10kΩ
0	0	1	OFF	ON	OFF	OFF	OFF	OFF	ON	OFF	-HV	10kΩ
0	1	0	ON	OFF	OFF	OFF	OFF	OFF	ON	OFF	+HV	10kΩ
0	1	1	OFF	OFF	ON	ON	ON	ON	OFF	ON	GND	HV <sub>OUT</sub> x
1	Х	Х	OFF	OFF	OFF	OFF	OFF	OFF	ON	OFF	HiZ	10kΩ

Note:  $V_{PP}/V_{NN}=+/-HV$ , x=1~8

Table 14 P1/N1 drive current mode

			lout	[A]
Current Mode	CC1	CC0	P1	N1
0	0	0	0.5	0.5
1	0	1	1	1
2	1	0	1.5	1.5
3	1	1	2	2

#### Note:

Recommended mode is as follows:

- Current mode 2 or 3 for high amplitude short cycle pulse waveforms, or for driving heavy load
- Current mode 0 or 1 for low amplitude long pulse train waveforms (e.g. CW), or for driving light load

Table 15 TRSW S1-S2 turn-on overlap time control mode

			S1-S2 ON
TRSW Control Mode	TR1	TR0	overlap time [ns]
0	0	0	0 (default)
1	0	1	100
2	1	0	200
3	1	1	300

Note: Detailed switching time diagram is shown in Fig.8.

# 7. Pin Configuration

Table 16 Pin Configuration

Pin#	Pin Name	I/O	Function
1	P <sub>IN</sub> 2		Logic input of channel 2
2	N <sub>IN</sub> 2	_	Logic input of channel 2
3	P <sub>IN</sub> 3	I	Logic input of channel 3
4	N <sub>IN</sub> 3	I	Logic input of channel 3
5	P <sub>IN</sub> 4	I	Logic input of channel 4
6	N <sub>IN</sub> 4	I	Logic input of channel 4
7	$V_{DD}$	-	Positive low voltage power supply (+5V)
8	CLK	I	Positive clock input (up to 200MHz)
9	CLKB	I	Negative clock Input (up to 200MHz)
10	GND	-	Drive power ground (0V)
11	P <sub>IN</sub> 5	I	Logic input of channel 5
12	N <sub>IN</sub> 5	I	Logic input of channel 5
13	P <sub>IN</sub> 6	I	Logic input of channel 6
14	N <sub>IN</sub> 6	I	Logic input of channel 6
15	P <sub>IN</sub> 7	I	Logic input of channel 7
16	N <sub>IN</sub> 7	I	Logic input of channel 7
17	P <sub>IN</sub> 8	I	Logic input of channel 8
18	N <sub>IN</sub> 8	I	Logic input of channel 8
19	CLKIF	I	Control of clock interface, Hi=differential CMOS, Low=LVDS (50kΩ internal pull-up resistor)
20	LV <sub>OUT</sub> 8	0	Low voltage output of channel 8
21	GND	-	Drive power ground (0V)
22	HV <sub>OUT</sub> 8	0	High voltage output of channel 8
23	V <sub>PP</sub>	-	Positive high voltage power supply (0 to +100V)
24	HV <sub>out</sub> 7	0	High voltage output of channel 7
25	V <sub>NN</sub>	-	Negative high voltage power supply (0 to -100V)
26	V <sub>FN</sub>	-	Built-in power supply for N-MOS (N1) gate drive
27	LV <sub>OUT</sub> 7	0	Low voltage output of channel 7
28	LV <sub>OUT</sub> 6	0	Low voltage output of channel 6
29	V <sub>FP</sub>	-	Built-in power supply for P-MOS (P1) gate drive
30	V <sub>PP</sub>	-	Positive high voltage power supply (0 to +100V)
31	HV <sub>OUT</sub> 6	0	High voltage output of channel 6
32	V <sub>NN</sub>	ı	Negative high voltage power supply (0 to -100V)

Table 16 Pin Configuration (cont.)

Pin#	Pin Name	I/O	Function
33	HV <sub>оит</sub> 5	0	High voltage output of channel 5
34	GND	-	Drive power ground (0V)
35	LV <sub>OUT</sub> 5	0	Low voltage output of channel 5
36	GND	-	Drive power ground (0V)
37	GND	-	Drive power ground (0V)
38	EN	I	Control of drive output enable, Hi=off, Low=on (50kΩ internal pull-up resistor)
39	Vss	-	Negative low voltage power supply (-5V)
40	V <sub>LL</sub>	-	Positive voltage supply of logic input interface (1.8 to 5V)
41	THP	0	Thermal protection output flag, open N-MOS drain
42	TR0	I	Lower bit of control of T/R switch S1 and S2 turn-on overlap time (50k $\Omega$ internal pull-down resistor)
43	TR1	I	Upper bit of control of T/R switch S1 and S2 turn-on overlap time (50k $\Omega$ internal pull-down resistor)
44	CC0	I	Lower bit of control of P1/N1 drive current (50kΩ internal pull-up resistor)
45	CC1	I	Upper bit of control of P1/N1 drive current (50kΩ internal pull-up resistor)
46	LV <sub>OUT</sub> 4	0	Low voltage output of channel 4
47	GND	-	Drive power ground (0V)
48	HV <sub>OUT</sub> 4	0	High voltage output of channel 4
49	V <sub>NN</sub>	-	Negative high voltage power supply (0 to -100V)
50	HV <sub>оит</sub> 3	0	High voltage output of channel 3
51	$V_{PP}$	-	Positive high voltage power supply (0 to +100V)
52	V <sub>FP</sub>	-	Built-in power supply for P-MOS (P1) gate drive
53	LV <sub>OUT</sub> 3	0	Low voltage output of channel 3
54	LV <sub>OUT</sub> 2	0	Low voltage output of channel 2
55	V <sub>FN</sub>	-	Built-in power supply for N-MOS (N1) gate drive
56	$V_{NN}$	-	Negative high voltage power supply (0 to -100V)
57	HV <sub>оит</sub> 2	0	High voltage output of channel 2
58	V <sub>PP</sub>	-	Positive high voltage power supply (0 to +100V)
59	HV <sub>OUT</sub> 1	0	High voltage output of channel 1
60	GND	-	Drive power ground (0V)
61	LV <sub>OUT</sub> 1	0	Low voltage output of channel 1
62	CLKEN	_	Control of clock enable, Hi=clock disable, Low=clock enable (50kΩ internal pull-up resistor)
63	P <sub>IN</sub> 1	I	Logic input of channel 1
64	N <sub>IN</sub> 1	_	Logic input of channel 1

### ■ Package

**Table 17 Package Drawing Codes** 

Package Name	Dimension	Tray	Marking	Land	Packing
QFN-64(0909)B	QN064-B-P-SD	QFN9x9-B-T-SD	QN064-B-M-S2	QN064-B-L-SD	QN064-B-K-SD

### ■ Storage, Mounting

#### 1. Storage conditions

- 1.1 The storage location should be kept at 5 to 35°C and 40 to 70% relative humidity. Keeping in a dry box is recommended. Moisture-proof property is assured for 12 months from delivery date for sealed moisture-proof packing, while it is guaranteed for 7 days from unpacked date under the condition above.
- 1. 2 When the storage conditions do not conform to those above or other conditions occur indicating moisture exposure, the ICs should be dried to avoid package cracks. A baking process at 125°C lasting for 24 hours results in sufficient dehumidification. The baking is not allowed more than twice, and the ICs should be mounted within 7 days after initial baking or within 10 days of total exposure after the second dehumidification.

#### 2. Reflow soldering

The temperature rise may be different in the resin and a terminal part due to the reflow soldering. It is necessary to check the package surface temperature (resin) before setting the temperature profile. **Fig. 9** shows the resistance to soldering heat condition for package (Reflow method). Confirm the heat resistance of the package shown below. (Based on JEDEC J-STD-020).

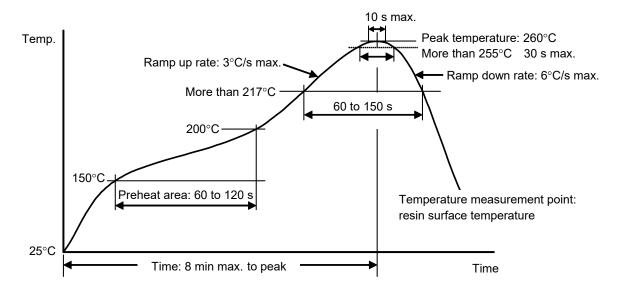


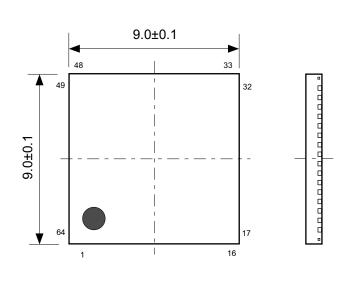
Fig. 9 Resistance to Soldering Heat Condition for Package (Reflow Method)

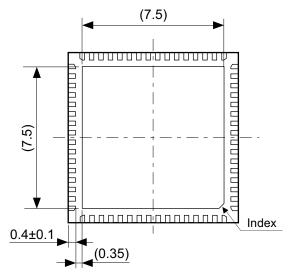
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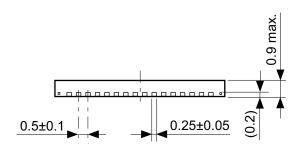
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  - **1.2** Those that touch products, such as work platform, machine, or measurement/test equipment, should be grounded.
  - 1.3 Those who deal with products should be grounded through a large series impedance around  $100k\Omega$  to  $1M\Omega$ .
  - **1.4** Prevent friction with other materials made with high polymer.
  - **1.5** Prevent vibration or friction when carrying the printed circuit board (PCB) where products are mounted. To short circuit terminals is a recommended countermeasure to keep the same electric potential on the PCB.
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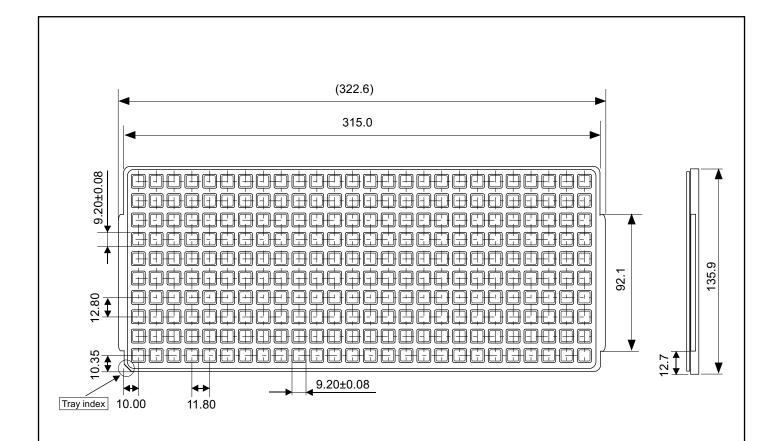


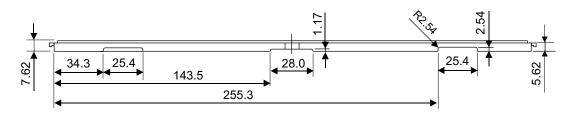


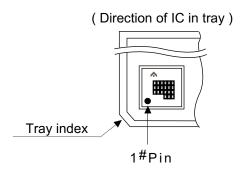


# No. QN064-B-P-SD-2.0

TITLE	QFN64-B-PKG Dimensions		
No.	QN064-B-P-SD-2.0		
ANGLE	$\bigoplus$		
UNIT	mm		
ABLIC Inc.			

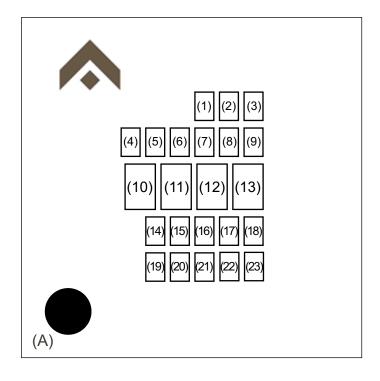






No. QFN9x9-B-T-SD-1.0

TITLE	QFN	9x9-B-Tr	ay
No.	QFN9	x9-B-T-SI	D-1.0
ANGLE		QTY.	260
UNIT	mm		
ABLIC Inc.			



(1) : Year of assembly

(2) : Month of assembly

(3) : Week of assembly

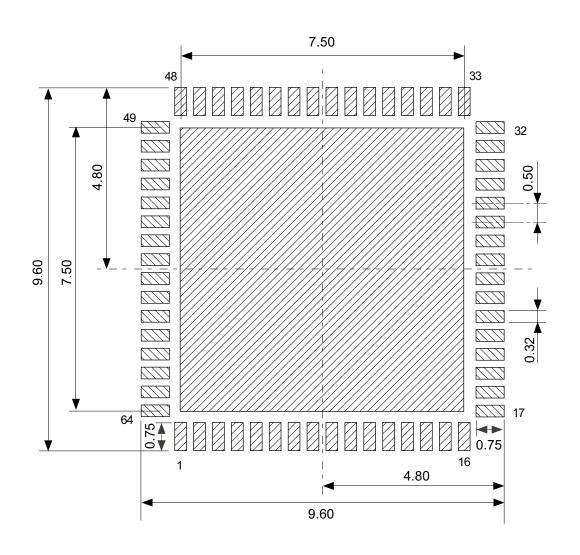
(4) to (13) : Product code

(14) to (23): Quality control code

(A) : 1-pin mark

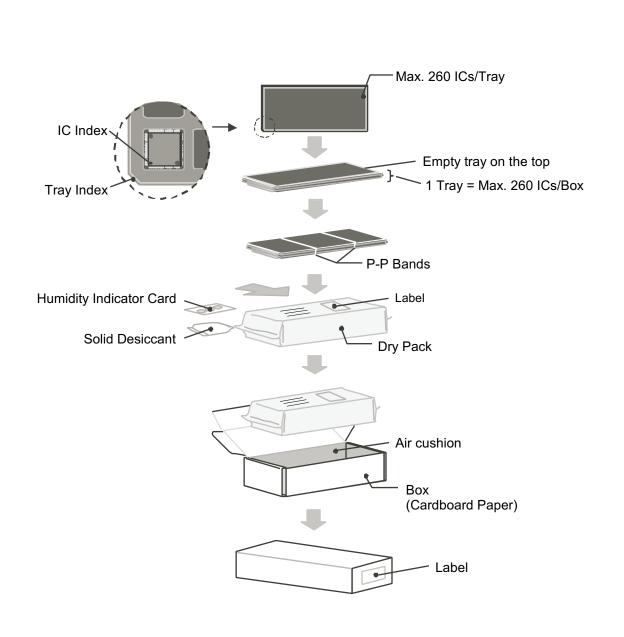
# No. QN064-B-M-S2-1.0

TITLE	QFN64-B-Markings (S-UM5543 / S-UM5584)			
No.	QN064-B-M-S2-1.0			
ANGLE				
UNIT	TYPE LASER			
ABLIC Inc.				



# No. QN064-B-L-SD-2.0

TITLE	QFN64-B -Land Recommendation		
No.	QN064-B-L-SD-2.0		
ANGLE			
UNIT	mm		
ABLIC Inc.			



# No. QN064-B-K-SD-2.0

TITLE	QFN64-B -Packing Procedure		
No.	QN064-B-K-SD-2.0		
ANGLE			
UNIT			
ABLIC Inc.			

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